

In the Claims

Please amend the claims as follows:

1(currently amended). A multilayered substrate for a semiconductor device, comprising: a multilayered substrate body formed of a plurality of conductor layers and insulation layers, and having a face for mounting a semiconductor element thereon and another face for external connection terminals, the face for mounting a semiconductor element comprising pads for mounting ~~through which the substrate is connected to the semiconductor element to be mounted thereon~~, and the face for external connection terminals comprising pads through which the substrate is connected to an external electrical circuit, wherein a reinforcing sheet joined to each of the face for mounting a semiconductor element thereon and the face for external connection terminals of the multilayered substrate body, and wherein the pads provided at the face for mounting a semiconductor element thereon are in the form of a bump so that the tip of the pads protrude ~~pad protrudes~~ from the face for mounting a semiconductor element of the multilayered substrate body.

2-11 (Cancelled).

12(currently amended). The multilayered substrate for a semiconductor device of claim 1, wherein the reinforcing sheet joined to the face for mounting a semiconductor element thereon is in the form of a frame and is made of a metal, and the frame is formed by etching a metal sheet on which the multilayered substrate body is formed so as to remove only the metal material in the region ~~where a semiconductor element is to be mounted~~ for mounting the semiconductor element.

13 (Cancelled).

14(currently amended). The multilayered substrate for a semiconductor device of claim 1, wherein the reinforcing sheet joined to the face for external connection terminals has through holes corresponding to the respective pads for the external connection terminals, ~~and the pads provided at the face for mounting a semiconductor element thereon are in the form of bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body.~~

15.(currently amended) The multilayered substrate for a semiconductor device of claim 1 wherein the reinforcing sheet joined to the face for external connection terminals is in the form of a frame. ,and wherein the pads provided at the face for mounting a semiconductor element thereon are in the form of a bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body

16-22 (Cancelled)

22.(currently amended) A multilayered substrate for a semiconductor device, comprising: a multilayered substrate body formed of a plurality of conductor layers and insulation layers, and having a face for mounting a semiconductor element thereon and another face for external connection terminals, the face for mounting a semiconductor element comprising pads for mounting the semiconductor element, and the face for external connection terminals comprising pads through which the substrate is connected to an external electrical circuit, wherein a reinforcing sheet joined to each of the face for mounting a semiconductor element thereon and the face for external connection terminals of the multilayered substrate body, and wherein the pads provided at the face for mounting a semiconductor element thereon are in the form of a bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body ~~The multilayered substrate for a semiconductor device of claim 1, wherein the reinforcing sheet joined to the face for mounting a semiconductor element thereon is in the form of a frame and is made of a metal, and the frame is formed by etching a metal sheet on which the multilayered substrate body is formed so as to remove the metal material in the region where a semiconductor element is to be mounted of the face for mounting the semiconductor element.~~

23. (Previously presented). The multilayered substrate for a semiconductor device of claim 22, wherein the reinforcing sheet comprises aluminum.

24. (Previously presented). The multilayered substrate for a semiconductor device of claim 22, wherein the reinforcing sheet comprises copper.

25. (Previously presented). The multilayered substrate for a semiconductor device of claim 22, wherein the reinforcing sheet comprises a nickel film.

26. (Previously presented). The multilayered substrate for a semiconductor device of claim 22, wherein the reinforcing sheet metal is treated to provide electrical insulation thereon.